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1. Electrical Specifications

Table 1. DC Electrical Specifications

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
3.3 V Operating Voltage	VDD core	3.3 ± 5%	3.135	3.3	3.465	V
3.3 V Input High Voltage	V _{IH}	Control input pins	2.0	—	V _{DD} + 0.3	V
3.3 V Input Low Voltage	V _{IL}	Control input pins	V _{SS} - 0.3	—	0.8	V
Input High Voltage	V _{IHI2C}	SDATA, SCLK	2.2	—	—	V
Input Low Voltage	V _{ILI2C}	SDATA, SCLK	—	—	1.0	V
Input High Leakage Current	I _{IH}	Except internal pull-down resistors, 0 < V _{IN} < V _{DD}	—	—	5	μA
Input Low Leakage Current	I _{IL}	Except internal pull-up resistors, 0 < V _{IN} < V _{DD}	-5	—	—	μA
3.3 V Output High Voltage (SE)	V _{OH}	I _{OH} = -1 mA	2.4	—	—	V
3.3 V Output Low Voltage (SE)	V _{OL}	I _{OL} = 1 mA	—	—	0.4	V
High-impedance Output Current	I _{OZ}		-10	—	10	μA
Input Pin Capacitance	C _{IN}		1.5	—	5	pF
Output Pin Capacitance	C _{OUT}			—	6	pF
Pin Inductance	L _{IN}		—	—	7	nH
Dynamic Supply Current	I _{DD_3.3V}	All outputs enabled. Differential clocks with 5" traces and 2 pF load.	—	—	40	mA

Table 2. AC Electrical Specifications

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal						
Long-term Accuracy	L_{ACC}	Measured at VDD/2 differential	—	—	250	ppm
Clock Input						
CLKIN Duty Cycle	T_{DC}	Measured at VDD/2	47	—	53	%
CLKIN Rise and Fall Times	T_R/T_F	Measured between 0.2 V _{DD} and 0.8 V _{DD}	0.5	—	4.0	V/ns
CLKIN Cycle to Cycle Jitter	T_{CCJ}	Measured at VDD/2	—	—	250	ps
CLKIN Long Term Jitter	T_{LTJ}	Measured at VDD/2	—	—	350	ps
Input High Voltage	V_{IH}	XIN/CLKIN pin	2	—	VDD+0.3	V
Input Low Voltage	V_{IL}	XIN/CLKIN pin	—	—	0.8	V
Input High Current	I_{IH}	XIN/CLKIN pin, VIN = VDD	—	—	35	μA
Input Low Current	I_{IL}	XIN/CLKIN pin, 0 < VIN < 0.8	-35	—	—	μA
DIFF at 0.7 V						
DIFF Duty Cycle	T_{DC}	Measured at 0 V differential	45	—	55	%
Any DIFF Clock Skew from the earliest bank to the latest bank	$T_{SKEW(window)}$	Measured at 0 V differential	—	—	50	ps
DIFF Cycle to Cycle Jitter	T_{CCJ}	Measured at 0 V differential	—	35	50	ps
Output PCIe Gen1 REFCLK Phase Jitter	RMS_{GEN1}	Includes PLL BW 1.5–22 MHz, $\zeta = 0.54$, Td=10 ns, Ftrk=1.5 MHz with BER = 1E-12	0	40	108	ps
Output PCIe Gen2 REFCLK Phase Jitter	RMS_{GEN2}	Includes PLL BW 8–16 MHz, Jitter Peaking = 3 dB, $\zeta = 0.54$, Td=12 ns, Low Band, F < 1.5 MHz	0	2	3.0	ps
Output PCIe Gen2 REFCLK Phase Jitter	RMS_{GEN2}	Includes PLL BW 8–16 MHz, Jitter Peaking = 3 dB, $\zeta = 0.54$, Td=12 ns, High Band, 1.5 MHz < F < Nyquist	0	2	3.1	ps
Output Phase Jitter Impact—PCIe Gen3	RMS_{GEN3}	Includes PLL BW 2 – 4 MHz, CDR = 10 MHz)	0	0.5	1.0	ps
DIFF Long Term Accuracy	L_{ACC}	Measured at 0 V differential	—	—	100	ppm
DIFF Rising/Falling Slew Rate	T_R / T_F	Measured differentially from ±150 mV	1	—	8	V/ns
Voltage High	V_{HIGH}		—	—	1.15	V
Voltage Low	V_{LOW}		-0.3	—	—	V
Crossing Point Voltage at 0.7 V Swing	V_{OX}		300	—	550	mV

Table 2. AC Electrical Specifications (Continued)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
REF(25 MHz) at 3.3 V						
Duty Cycle	T_{DC}	Measurement at 1.5 V	45	—	55	%
Rising and Falling Edge Rate	T_R / T_F	Measured between 0.8 and 2.0 V	1.0	—	4.0	V/ns
Cycle to Cycle Jitter	T_{CCJ}	Measurement at 1.5 V	—	—	300	ps
Long Term Accuracy	L_{ACC}	Measured at 1.5 V	—	—	100	ppm
Enable/Disable and Set-Up						
Clock Stabilization from Power-up	T_{STABLE}		—	—	1.8	ms
Stopclock Set-up Time	T_{SS}		10.0	—	—	ns

Table 3. Absolute Maximum Conditions

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Main Supply Voltage	$V_{DD_3.3V}$	Functional	—	—	4.6	V
Input Voltage	V_{IN}	Relative to V_{SS}	-0.5	—	4.6	V_{DC}
Temperature, Storage	T_S	Non-functional	-65	—	150	°C
Temperature, Operating Ambient	T_A	Functional	-40	—	85	°C
Temperature, Junction	T_J	Functional	—	—	150	°C
Dissipation, Junction to Case	θ_{JC}	JEDEC (JESD 51)	—	—	35	°C/W
Dissipation, Junction to Ambient	θ_{JA}	JEDEC (JESD 51)	—	—	37	°C/W
ESD Protection (Human Body Model)	ESD_{HBM}	JEDEC (JESD 22-A114)	2000	—	—	V
Flammability Rating	UL-94	UL (Class)	V-0			
Moisture Sensitivity Level	MSL	JEDEC (J-STD-020)	2			
Note: While using multiple power supplies, the voltage on any input or I/O pin cannot exceed the power pin during power-up. Power supply sequencing is not required.						

2. Functional Description

2.1. Crystal Recommendations

The clock device requires a parallel resonance crystal. Substituting a series resonance crystal causes the clock device to operate at the wrong frequency and violates the ppm specification. For most applications there is a 300 ppm frequency shift between series and parallel crystals due to incorrect loading.

Table 4. Crystal Recommendations

Frequency (Fund)	Cut	Loading	Load Cap	Shunt Cap (max)	Motional (max)	Tolerance (max)	Stability (max)	Aging (max)
25 MHz	AT	Parallel	12–15 pF	5 pF	0.016 pF	35 ppm	30 ppm	5 ppm

2.1.1. Crystal Loading

Crystal loading plays a critical role in achieving low ppm performance. To realize low ppm performance, use the total capacitance the crystal sees to calculate the appropriate capacitive loading (CL).

Figure 1 shows a typical crystal configuration using the two trim capacitors. It is important that the trim capacitors are in series with the crystal. It is not true that load capacitors are in parallel with the crystal and are approximately equal to the load capacitance of the crystal.

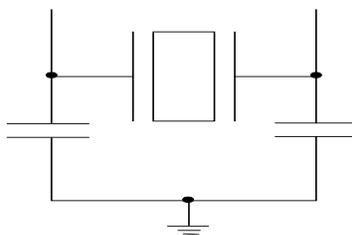


Figure 1. Crystal Capacitive Clarification

2.1.2. Calculating Load Capacitors

In addition to the standard external trim capacitors, consider the trace capacitance and pin capacitance to calculate the crystal loading correctly. Again, the capacitance on each side is in series with the crystal. The total capacitance on both side is twice the specified crystal load capacitance (CL). Trim capacitors are calculated to provide equal capacitive loading on both sides.

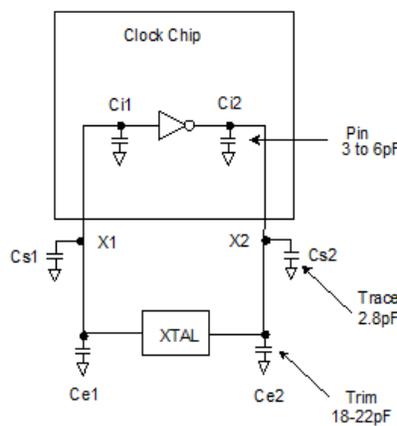


Figure 2. Crystal Loading Example

Use the following formulas to calculate the trim capacitor values for Ce1 and Ce2.

Load Capacitance (each side)

$$C_e = 2 \times CL - (C_s + C_i)$$

Total Capacitance (as seen by the crystal)

$$CL_e = \frac{1}{\left(\frac{1}{C_{e1} + C_{s1} + C_{i1}} + \frac{1}{C_{e2} + C_{s2} + C_{i2}} \right)}$$

- CL: Crystal load capacitance
- CL_e: Actual loading seen by crystal using standard value trim capacitors
- Ce: External trim capacitors
- Cs: Stray capacitance (terraced)
- Ci : Internal capacitance (lead frame, bond wires, etc.)

2.2. OE Clarification

The OE pins are active high inputs used to enable and disable the output clocks. To enable the output clock, the OE pin needs to be logic high and the I²C output enable bit needs to be logic high. There are two methods to disable the output clocks: the OE is pulled to a logic low, or the I²C enable bit is set to a logic low. The OE pins is required to be driven at all time and even though it has an internally 100 kΩ resistor.

2.3. OE Assertion

The OE signals are active high input used for synchronous stopping and starting the output clocks respectively while the rest of the clock generator continues to function. The assertion of the OE signal by making it logic high causes stopped respective output clocks to resume normal operation. No short or stretched clock pulses are produced when the clock resumes. The maximum latency from the assertion to active outputs is no more than two to six output clock cycles.

2.4. OE Deassertion

When the OE pin is deasserted by making its logic low, the corresponding output clocks are stopped cleanly, and the final output state is driven low.

2.5. SS[1:0] Clarification

SS[1:0] are active inputs used to select differential output frequency and enable spread of –0.5% on all DIFF outputs as per Table 5.

Table 5. SS0 and SS1 Frequency/Spread Selection

SS1	SS0	Differential Frequency	Differential Spread	Configuration
0	0	100 MHz	Spread Off	Default
0	1	100 MHz	–0.50%	
1	0	125 MHz	Spread Off	
1	1	200 MHz	Spread Off	

3. Test and Measurement Setup

This diagram shows the test load configuration for the differential clock signals.

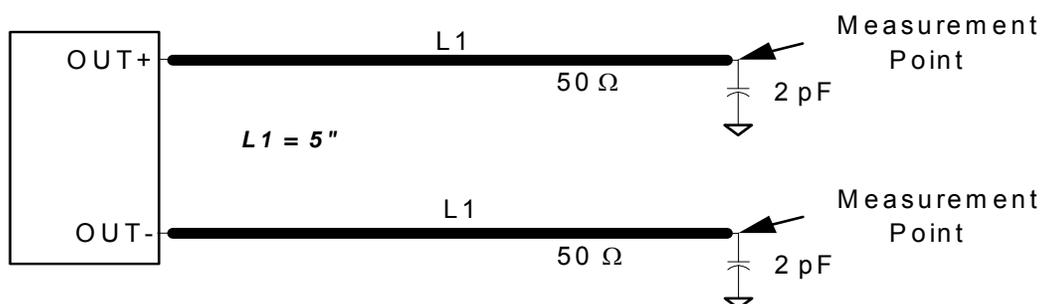
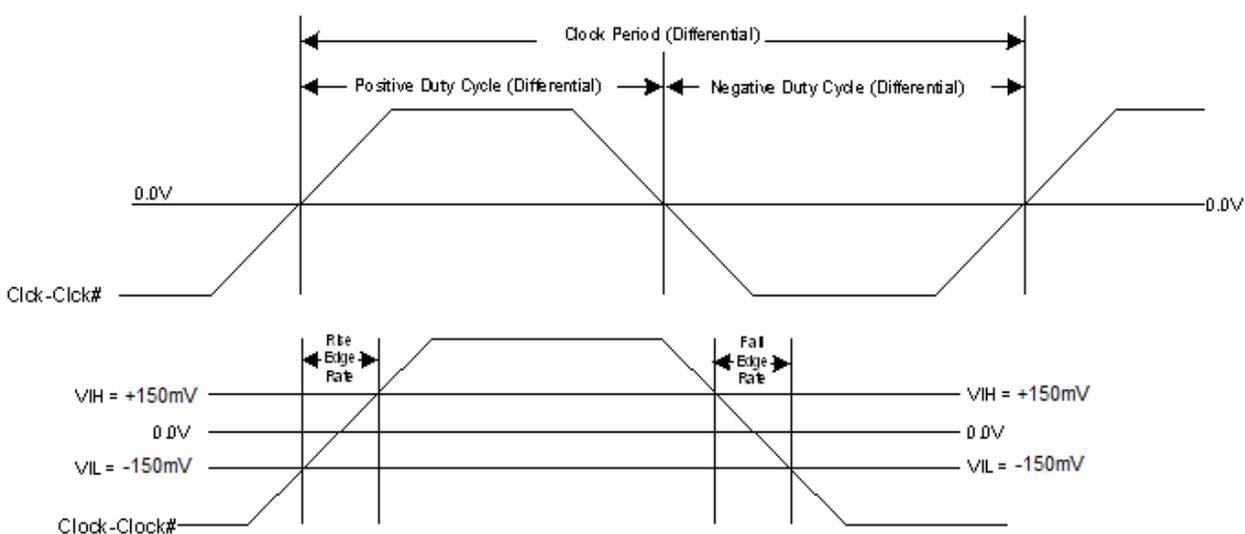


Figure 3. 0.7 V Differential Load Configuration



**Figure 4. Differential Measurement for Differential Output Signals
(for AC Parameters Measurement)**

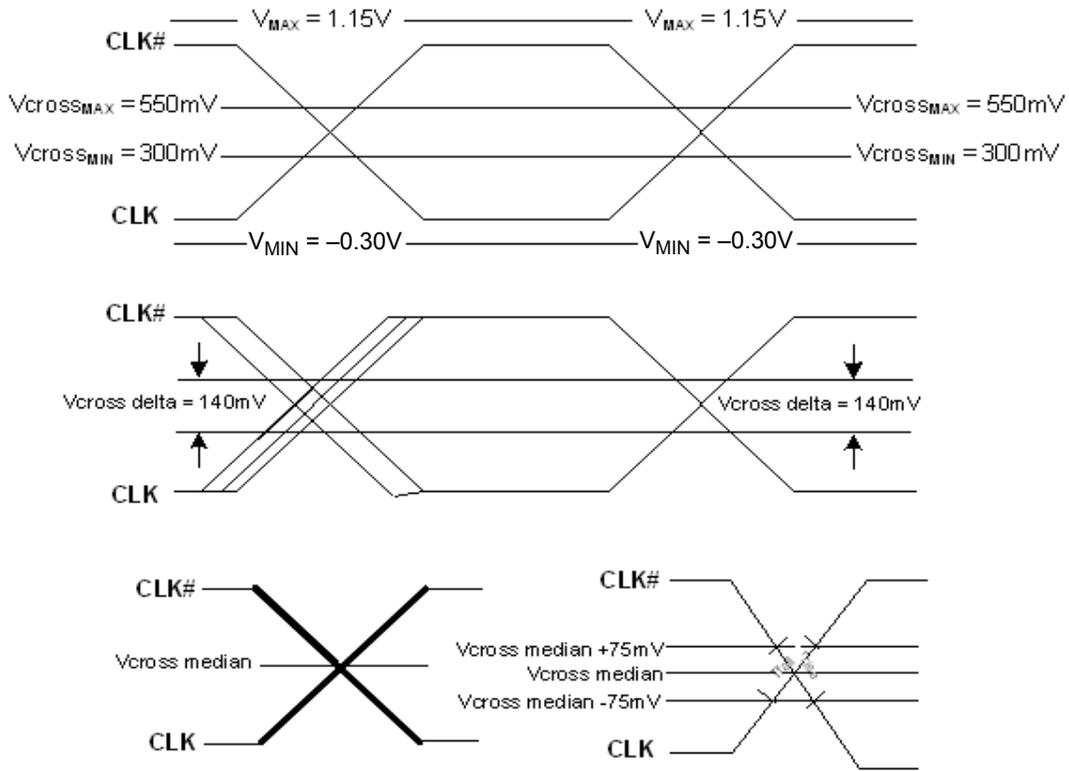


Figure 5. Single-ended Measurement for Differential Output Signals (for AC Parameters Measurement)

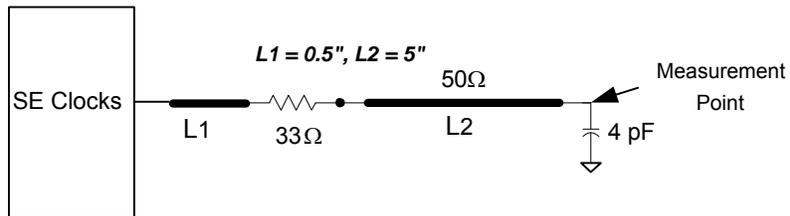


Figure 6. Single-ended Clocks with Single Load Configuration

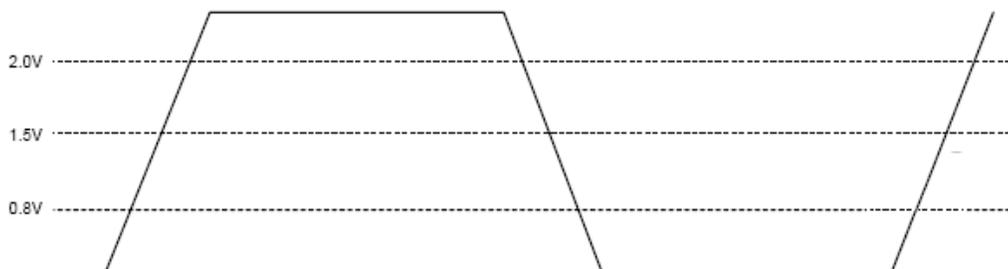


Figure 7. Single-ended Output Signal (for AC Parameter Measurement)

4. Control Registers

4.1. Serial Data Interface

To enhance the flexibility and function of the clock synthesizer, a two-signal serial interface is provided. Through the Serial Data Interface, various device functions, such as individual clock output buffers are individually enabled or disabled. The registers associated with the Serial Data Interface initialize to their default setting at power-up. The use of this interface is optional. Clock device register changes are normally made at system initialization, if any are required. The interface cannot be used during system operation for power management functions.

4.2. Data Protocol

The clock driver serial protocol accepts byte write, byte read, block write, and block read operations from the controller. For block write/read operation, access the bytes in sequential order from lowest to highest (most significant bit first) with the ability to stop after any complete byte is transferred. For byte write and byte read operations, the system controller can access individually indexed bytes. The offset of the indexed byte is encoded in the command code described in Table 1 on page 4.

The block write and block read protocol is outlined in Table 6 while Table 7 outlines byte write and byte read protocol. The slave receiver address is 11010110 (D6h).

Table 6. Block Read and Block Write Protocol

Block Write Protocol		Block Read Protocol	
Bit	Description	Bit	Description
1	Start	1	Start
8:2	Slave address—7 bits	8:2	Slave address—7 bits
9	Write	9	Write
10	Acknowledge from slave	10	Acknowledge from slave
18:11	Command Code—8 bits	18:11	Command Code—8 bits
19	Acknowledge from slave	19	Acknowledge from slave
27:20	Byte Count—8 bits	20	Repeat start
28	Acknowledge from slave	27:21	Slave address—7 bits
36:29	Data byte 1—8 bits	28	Read = 1
37	Acknowledge from slave	29	Acknowledge from slave
45:38	Data byte 2—8 bits	37:30	Byte Count from slave—8 bits
46	Acknowledge from slave	38	Acknowledge
....	Data Byte /Slave Acknowledges	46:39	Data byte 1 from slave—8 bits
....	Data Byte N—8 bits	47	Acknowledge
....	Acknowledge from slave	55:48	Data byte 2 from slave—8 bits
....	Stop	56	Acknowledge
		Data bytes from slave/Acknowledge
		Data Byte N from slave—8 bits
		NOT Acknowledge
		Stop

Table 7. Byte Read and Byte Write Protocol

Byte Write Protocol		Byte Read Protocol	
Bit	Description	Bit	Description
1	Start	1	Start
8:2	Slave address–7 bits	8:2	Slave address–7 bits
9	Write	9	Write
10	Acknowledge from slave	10	Acknowledge from slave
18:11	Command Code–8 bits	18:11	Command Code–8 bits
19	Acknowledge from slave	19	Acknowledge from slave
27:20	Data byte–8 bits	20	Repeated start
28	Acknowledge from slave	27:21	Slave address–7 bits
29	Stop	28	Read
		29	Acknowledge from slave
		37:30	Data from slave–8 bits
		38	NOT Acknowledge
		39	Stop

Control Register 0. Byte 0

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name						REF_OE		
Type	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Reset settings = 00000100

Bit	Name	Function
7:3	Reserved	
2	REF_OE	Output Enable for REF. 0: Output disabled. 1: Output enabled.
1:0	Reserved	

Control Register 1. Byte 1

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name								
Type	R/W							

Reset settings = 00000000

Bit	Name	Function
7:0	Reserved	

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Control Register 2. Byte 2

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name	DIFF0_OE	DIFF1_OE						
Type	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Reset settings = 11000000

Bit	Name	Function
7	DIFF0_OE	Output Enable for DIFF0. 0: Output disabled. 1: Output enabled.
6	DIFF1_OE	Output Enable for DIFF1. 0: Output disabled. 1: Output enabled.
5:0	Reserved	

Control Register 3. Byte 3

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name	Rev Code[3:0]				Vendor ID[3:0]			
Type	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Reset settings = 00001000

Bit	Name	Function
7:4	Rev Code[3:0]	Program Revision Code.
3:0	Vendor ID[3:0]	Vendor Identification Code.

Control Register 4. Byte 4

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name	BC[7:0]							
Type	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Reset settings = 00000110

Bit	Name	Function
7:0	BC[7:0]	Byte Count Register.

Control Register 5. Byte 5

Bit	D7	D6	D5	D4	D3	D2	D1	D0
Name	DIFF_Amp_Sel	DIFF_Amp_Cntl[2]	DIFF_Amp_Cntl[1]	DIFF_Amp_Cntl[0]				
Type	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Reset settings = 11011000

Bit	Name	Function
7	DIFF_Amp_Sel	Amplitude Control for DIFF Differential Outputs. 0: Differential outputs with Default amplitude. 1: Differential outputs amplitude is set by Byte 5[6:4].
6	DIFF_Amp_Cntl[2]	DIFF Differential Outputs Amplitude Adjustment. 000: 300 mV 001: 400 mV 010: 500 mV 011: 600 mV 100: 700 mV 101: 800 mV 110: 900 mV 111: 1000 mV
5	DIFF_Amp_Cntl[1]	
4	DIFF_Amp_Cntl[0]	
3:0	Reserved	

5. Pin Descriptions: 24-Pin QFN

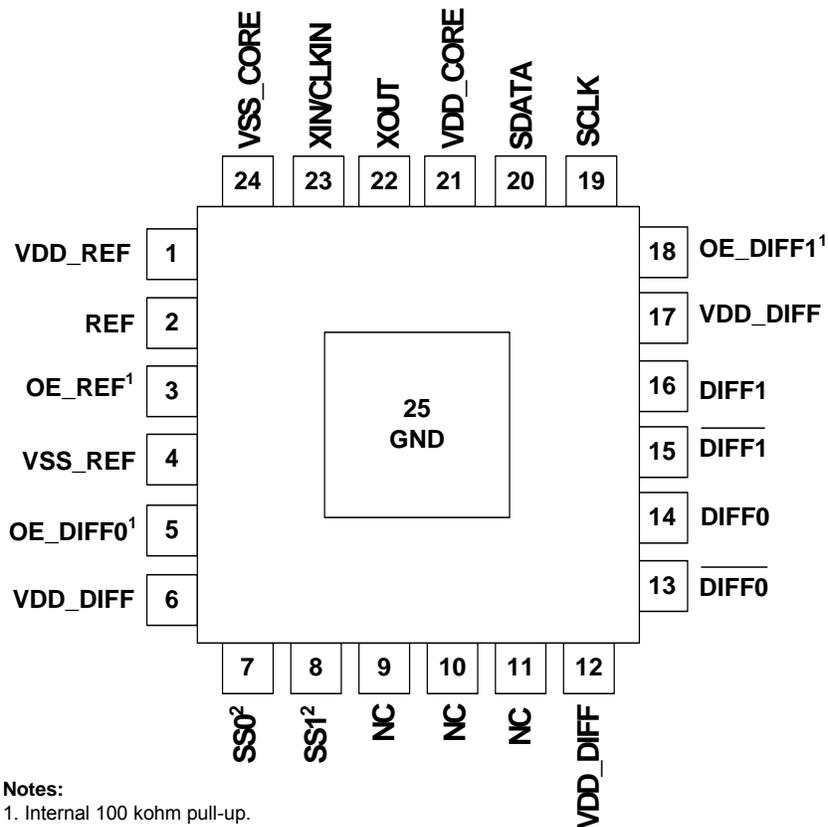


Table 8. Si52142 24-Pin QFN Descriptions

Pin #	Name	Type	Description
1	VDD_REF	PWR	3.3 V Power Supply
2	REF	O, SE	3.3 V, 25 MHz crystal reference clock
3	OE_REF	I,PU	3.3 V input to disable REF Clock (internal 100 kΩ pull-up). Refer to Table 1 on page 4 for OE specifications.
4	VSS_REF	GND	Ground
5	OE_DIFF0	I,PU	3.3 V input to disable DIFF0 (internal 100 kΩ pull-up). Refer to Table 1 on page 4 for OE specifications.
6	VDD_DIFF	PWR	3.3 V Power Supply
7	SS0	I, PD	3.3 V tolerant latch-input for enabling Frequency/ Spread selection on DIFF0 and DIFF1 outputs. Refer to Table 1 on page 4 for SS[1:0] specifications.
8	SS1	I, PD	
9	NC	NC	No Connect
10	NC	NC	No Connect

Table 8. Si52142 24-Pin QFN Descriptions (Continued)

Pin #	Name	Type	Description
11	NC	NC	No Connect
12	VDD_DIFF	PWR	3.3 V power supply
13	$\overline{\text{DIFF0}}$	O, DIF	0.7 V, 100 MHz differential clock
14	DIFF0	O, DIF	0.7 V, 100 MHz differential clock
15	$\overline{\text{DIFF1}}$	O, DIF	0.7 V, 100 MHz differential clock
16	DIFF1	O, DIF	0.7 V, 100 MHz differential clock
17	VDD_DIFF	PWR	3.3 V power supply
18	OE_DIFF1	I,PU	3.3 V input to disable DIFF1 (internal 100 k Ω pull-up). Refer to Table 1 on page 4 for OE specifications.
19	SCLK	I	SMBus compatible SCLOCK
20	SDATA	I/O	SMBus compatible SDATA
21	VDD_CORE	PWR	3.3 V power supply
22	XOUT	O	25.00 MHz Crystal output, Float XOUT if using only CLKIN (Clock input)
23	XIN/CLKIN	I	25.00 MHz Crystal input or 3.3 V, 25 MHz Clock Input
24	VSS_CORE	GND	Ground
25	GND	GND	Ground for bottom pad of the IC

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6. Ordering Guide

Part Number	Package Type	Temperature
Lead-free		
Si52142-A01AGM	24-pin QFN	Industrial, -40 to 85 °C
Si52142-A01AGMR	24-pin QFN—Tape and Reel	Industrial, -40 to 85 °C

7. Package Outline

Figure 8 illustrates the package details for the Si52142. Table 9 lists the values for the dimensions shown in the illustration.

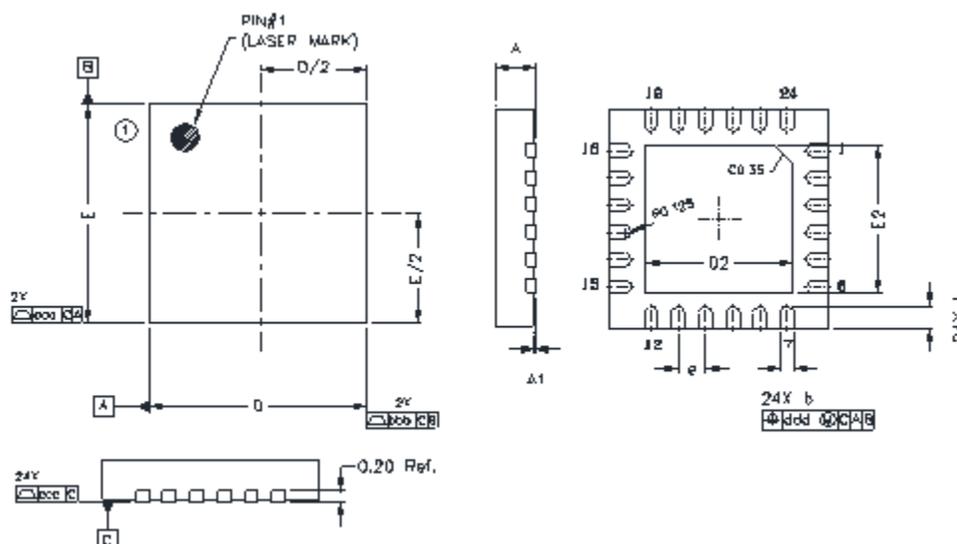


Figure 8. 24-Pin Quad Flat No Lead (QFN) Package

Table 9. Package Diagram Dimensions

Symbol	Millimeters		
	Min	Nom	Max
A	0.70	0.75	0.80
A1	0.00	0.025	0.05
b	0.20	0.25	0.30
D	4.00 BSC		
D2	2.60	2.70	2.80
e	0.50 BSC		
E	4.00 BSC		
E2	2.60	2.70	2.80
L	0.30	0.40	0.50
aaa	0.10		
bbb	0.10		
ccc	0.08		
ddd	0.07		
Notes:			
1. All dimensions shown are in millimeters (mm) unless otherwise noted.			
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.			
3. This drawing conforms to JEDEC outline MO-220, variation VGGD-8.			
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.			

CONTACT INFORMATION

Silicon Laboratories Inc.

400 West Cesar Chavez
Austin, TX 78701
Tel: 1+(512) 416-8500
Fax: 1+(512) 416-9669
Toll Free: 1+(877) 444-3032

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